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PATENT  
03345-P0013A WWW/DC

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	Bernd Schoettker
Serial No. 09/624,252	Filing Date: July 24, 2000
Title of Application	Method For Growing Nitrogenous Semiconductor Crystal Materials
Group Art Unit	Examiner

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Assistant Commissioner for Patents  
Washington, DC 20231

Response to First Office Action

In response to the First Official Action dated December 6, 2001, Applicant submits the following Amendments and Remarks.

Version of Marked Up Claims:

1. (Amended) MOCVD process for the initial growth of nitrogenous semiconductor crystal materials in the form of  $A_xB_yC_zN_vM_w$  wherein A,B,C, is an element of group II or III, N is nitrogen, M represents an element of group V or VI, and X,Y,Z,W denote the molar fraction of each element of this compound, which are deposited on sapphire, SiC or Si, characterized in that the deposition of these semiconductor materials is performed in a continuous growth process from the first moment of wafer covering up to the achievement of a high-quality stratum on the surface, whereby the growth starts at a low initial growth temperature, which increases by means of a ramp function to the common high growth temperature.

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February 20, 2002

Lori J. Giuffrida

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4. (Twice Amended) Process according to Claim 1,  
characterized by controlling the stress density in the semiconductor crystal by a  
continuous variation of the growth regime during the initial growth by means of ramp  
functions [(e.g. hexagonal and cubic phase)].

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